MBR7030WTG

Switch-mode Power Rectifier

The switch-mode power rectifier, a state-of-the-art device, employs the use of the Schottky Barrier principle with a Platinum barrier metal.

Features

- Dual Diode Construction; Terminals 1 and 3 May Be Connected for Parallel Operation at Full Rating
- 30 V Blocking Voltage
- Low Forward Voltage Drop
- Guardring for Stress Protection and High dv/dt Capability
- 175°C Operating Junction Temperature
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

Mechanical Characteristics

- Case: Epoxy, Molded. Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 4.3 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Ratings: Machine Model, B (< 400 V)
 - Human Body Model, 3B (> 8000 V)

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	V
Average Rectified Forward Current (Rated V_R , $T_C = 100^{\circ}C$) Per Leg Per Device	I _{F(AV)}	35 70	A
Peak Repetitive Forward Current, (Rated V _R , Square Wave, 20 kHz, T _C = 100°C)	I _{FRM}	70	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	500	A
Peak Repetitive Reverse Current (2.0 μs, 1.0 kHz)	I _{RRM}	2.0	Α
Storage Temperature Range	T _{stg}	-55 to +175	°C
Operating Junction Temperature (Note 1)	TJ	-55 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

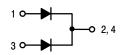
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

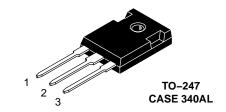


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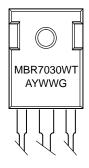
http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 70 AMPERES, 30 VOLTS





MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MBR7030WTG	TO-247 (Pb-Free)	30 Units/Rail

MBR7030WTG

THERMAL CHARACTERISTICS (Per Diode)

Rating	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	0.55	°C/W
ELECTRICAL CHARACTERISTICS (Per Diode)	·		
Instantaneous Forward Voltage (Note 2) @ $I_F = 35$ Amps, $T_C = 25^{\circ}C$ @ $I_F = 70$ Amps, $T_C = 25^{\circ}C$ @ $I_F = 35$ Amps, $T_C = 100^{\circ}C$	V _F	0.55 0.72 0.52	V
Instantaneous Reverse Current (Note 2) @ Rated DC Voltage, T _C = 25°C	I _R	5.0	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 µs, Duty Cycle < 2.0%

@ Rated DC Voltage, T_C = 100°C

TYPICAL CHARACTERISTICS

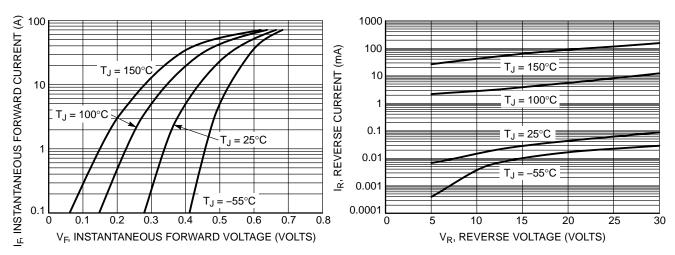


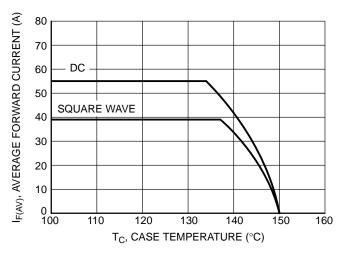
Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

250

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TYPICAL CHARACTERISTICS



P_{F(AV)}, AVERAGE POWER DISSIPATION (WATTS) 45 40 35 SQUARE 30 WAVE 25 20 DC 15 10 5 30 40 50 60 $I_{F(AV)}$, AVERAGE FORWARD CURRENT (AMPS)

Figure 3. Current Derating (Case)

Figure 4. Forward Power Dissipation (Per Leg)

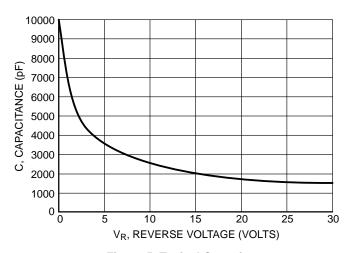
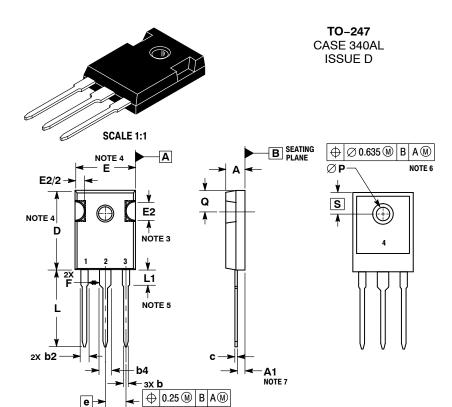


Figure 5. Typical Capacitance



DATE 17 MAR 2017

- NOTES:

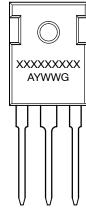
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.

 - DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY
 - LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY
- ©P SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.

 DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.70	5.30	
A1	2.20	2.60 1.33	
b	1.07		
b2	1.65	2.35	
b4	2.60	3.40	
С	0.45	0.68	
D	20.80	21.34 16.25	
E	15.50		
E2	4.32	5.49	
е	5.45 BSC		
F	2.655		
L	19.80	20.80	
L1	3.81	4.32	
P	3.55	3.65	
Q	5.40	6.20	
S	6.15 BSC		

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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